N-Channel 100-V (D-S) MOSFET

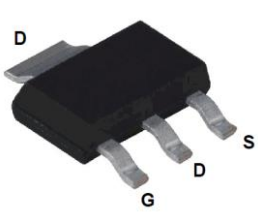
Key Features:
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

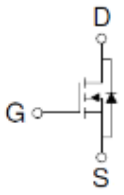
Typical Applications:
- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (mΩ)	I_D (A)
100	210 @ V_{GS} = 10V	2.6

Pb-free
RoHS COMPLIANT
HALOGEN FREE

SOT-223





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current [a]	T_C=25°C	I_D	2.6	A
Pulsed Drain Current [b]		I_{DM}	10	
Continuous Source Current (Diode Conduction) [a]		I_S	2.6	A
Power Dissipation [a]	T_C=25°C	P_D	2.1	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient [a]	$R_{\theta JA}$	40	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

Electrical Characteristics

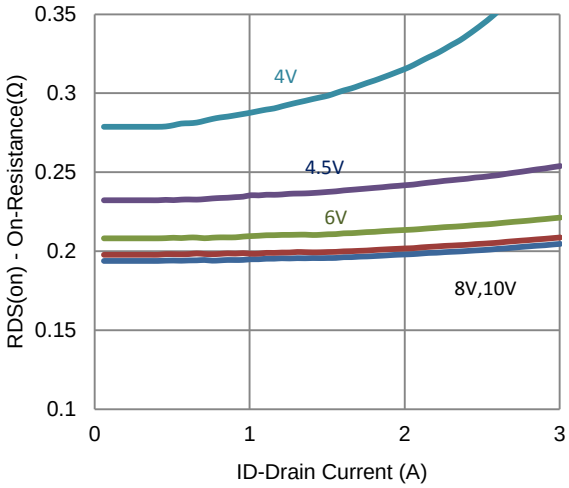
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	uA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current [a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	3.9			A
Drain-Source On-Resistance [a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 2.1 A			210	mΩ
Forward Transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 2.1 A		5		S
Diode Forward Voltage [a]	V_{SD}	I_S = 1.3 A, V_{GS} = 0 V		0.79		V
Dynamic [b]						
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 2.1 A		8.5		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			2.9		
Turn-On Delay Time	$t_{d(on)}$	V_{DS} = 50 V, R_L = 23.9 Ω, I_D = 2.1 A, V_{GEN} = 10 V, R_{GEN} = 6 Ω		5		ns
Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			12		
Fall Time	t_f			3		
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 Mhz		278		pF
Output Capacitance	C_{oss}			32		
Reverse Transfer Capacitance	C_{rss}			23		

Notes

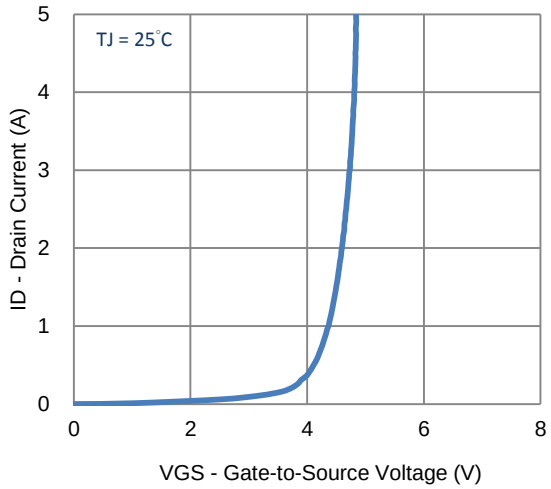
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

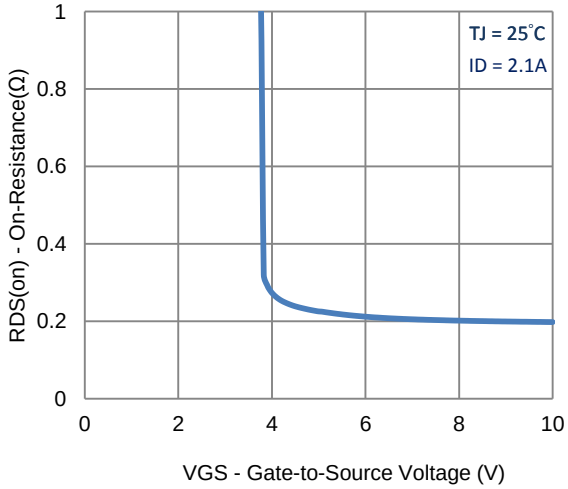
Typical Electrical Characteristics



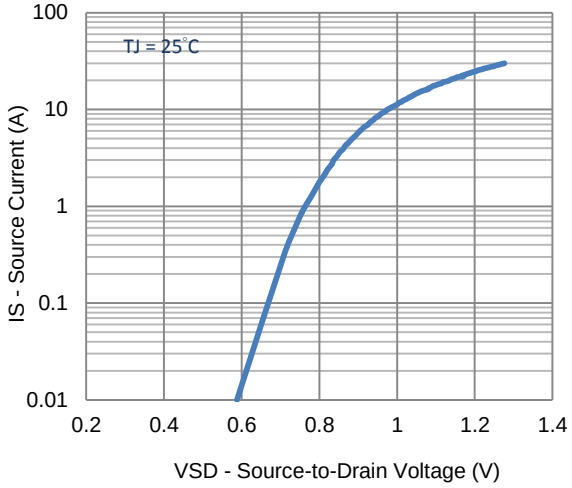
1. On-Resistance vs. Drain Current



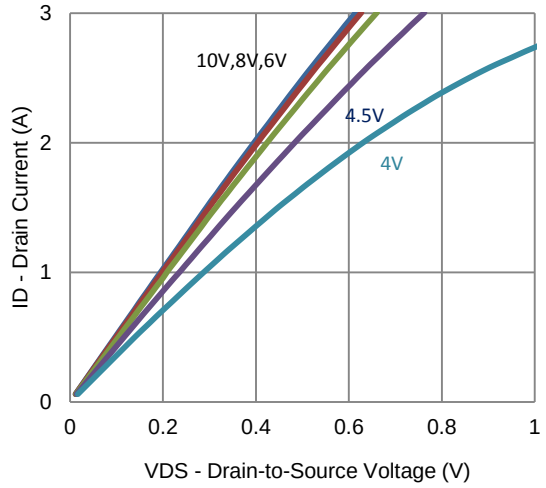
2. Transfer Characteristics



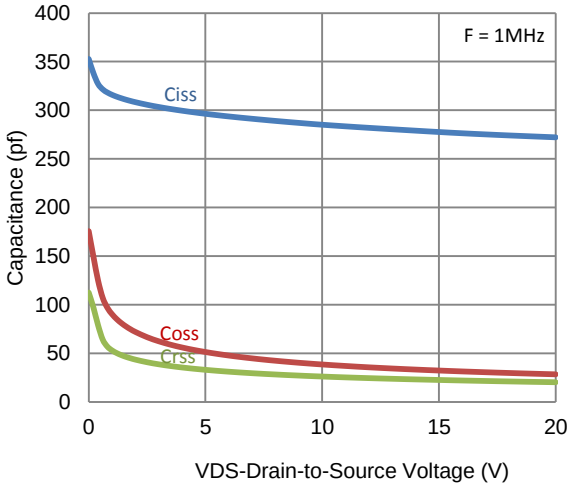
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

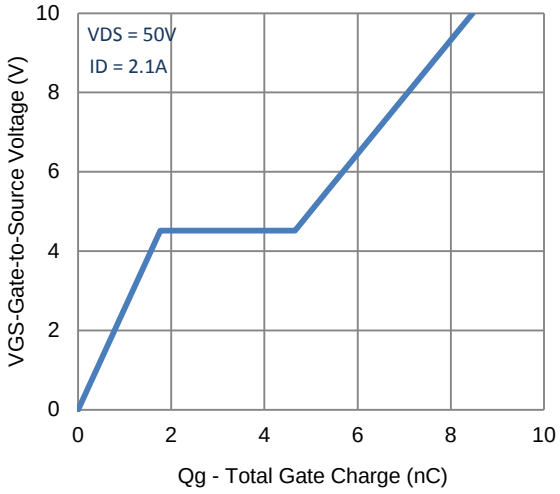


5. Output Characteristics

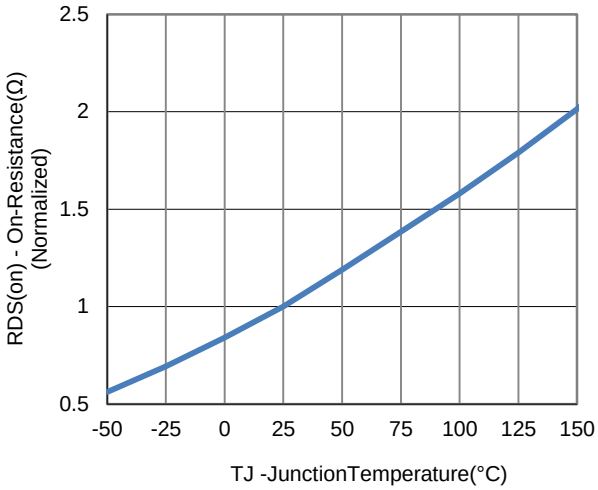


6. Capacitance

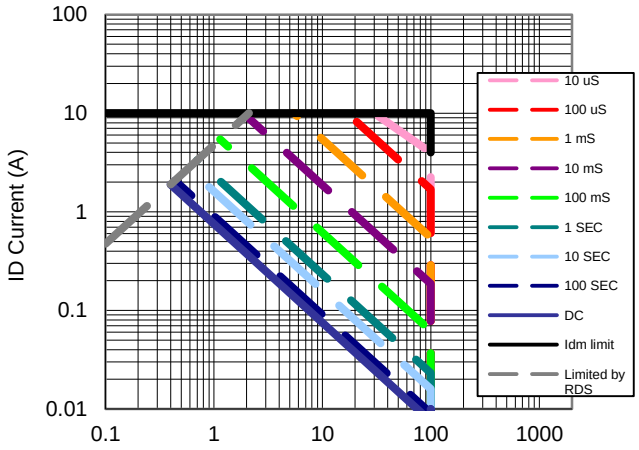
Typical Electrical Characteristics



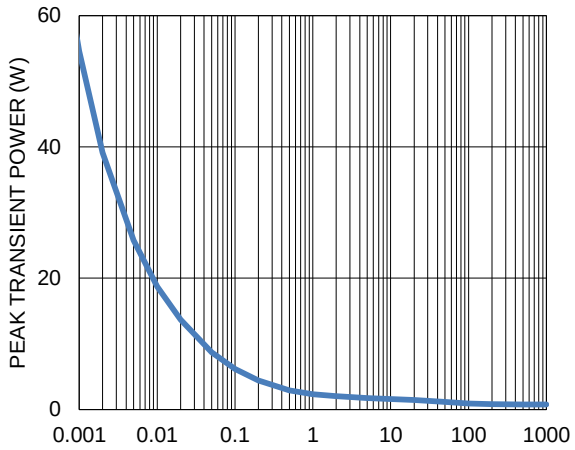
7. Gate Charge



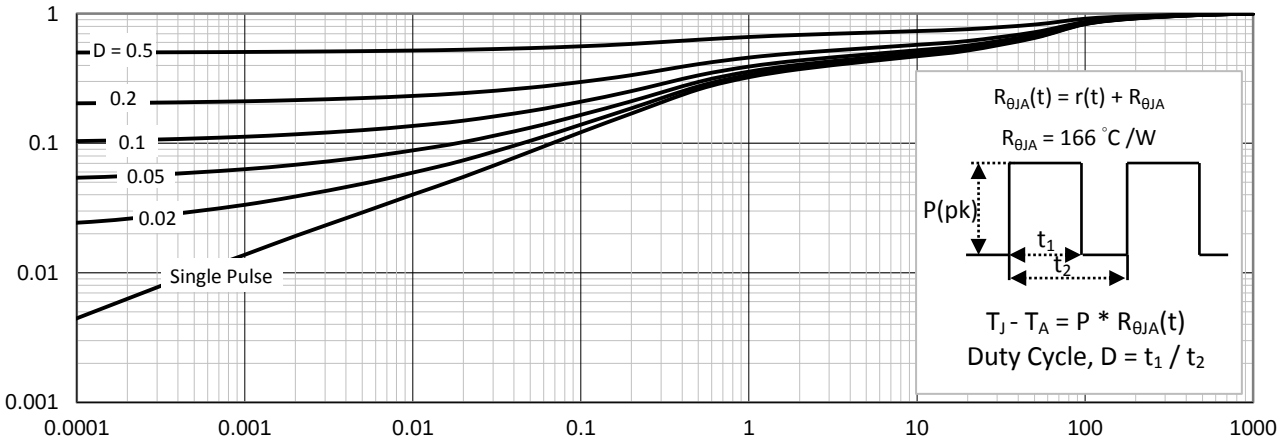
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

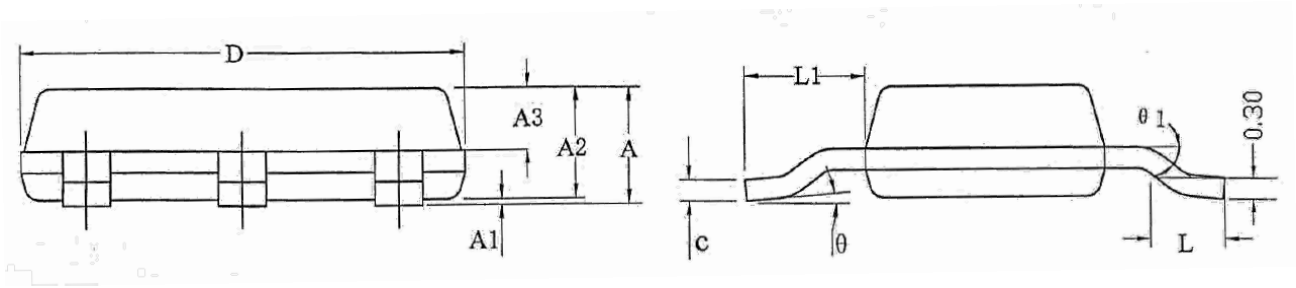


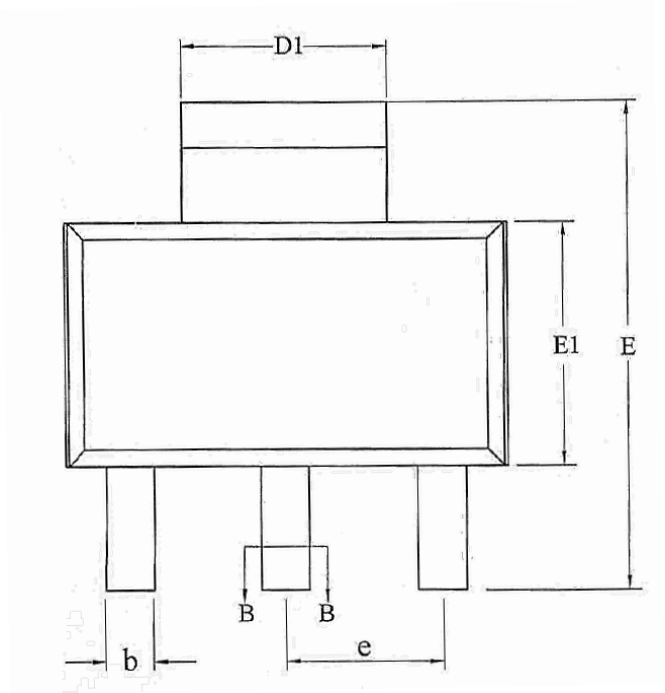
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.50	1.65	1.80
A1	0.03	0.06	0.09
A2	1.45	1.60	1.75
A3	0.80	0.90	1.00
b	0.69	—	0.78
b1	0.68	0.71	0.74
c	0.30	—	0.35
c1	0.29	0.30	0.31
D	6.30	6.50	6.70
D1	3.00REF		
E	6.80	7.00	7.20
E1	3.40	3.50	3.60
e	2.30BSC		
	0.90	—	—
L1	1.75BSC		
θ	0	—	7°
θ1	37.5 REF		